

Transistors with Built-in Resistor DRA5124E0L

DRA5124E0L Silicon PNP epitaxial planar type

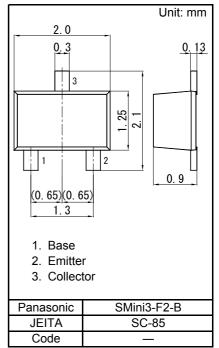
For digital circuits Complementary to DRC5124E DRA2124E in SMini3 type package

Features

- Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: LE

Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



int .	_			
V V nA	Internal	Con	nectior	ı
ıW °C		᠇ᢩᠺ	oC	
2° 2°	R ₂		•E	
	Resistance	R1	22	kΩ
	value	R2	22	kΩ

■ Absolute Maximum Ratings Ta = 25 °C

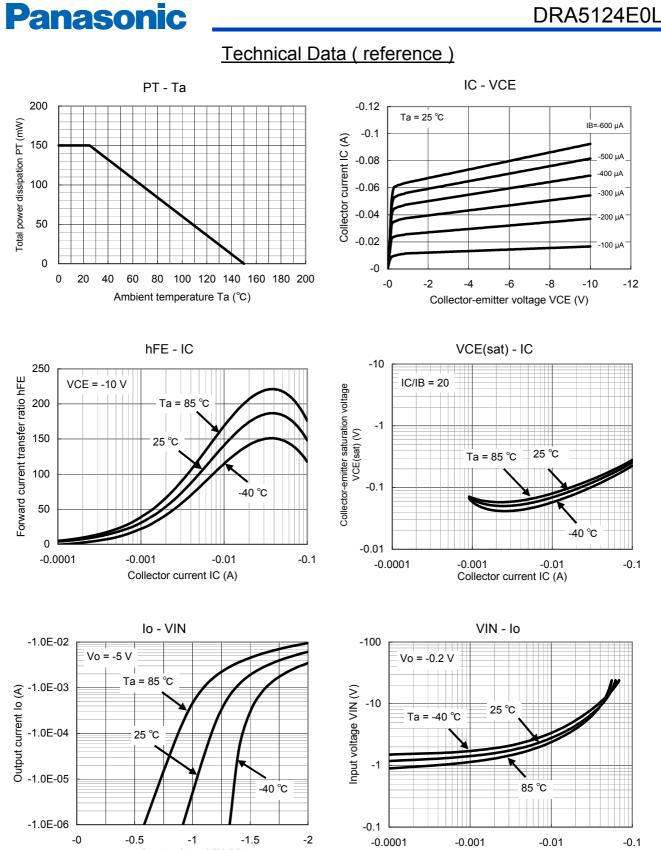
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	VCBO	-50	V	
Collector-emitter voltage (Base open)	VCEO	-50	V	
Collector current	IC	-100	mA	
Total power dissipation	PT	150	mW	
Junction temperature	Tj	150	°C	
Operating ambient temperature	Topr	-40 to +85	°C	
Storage temperature	Tstg	-55 to +150	С°	

Electrical Characteristics	5 Ta = 25 °C ± 3 °C
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Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	VCBO	IC = -10 μA, IE = 0	-50			V
Collector-emitter voltage (Base open)	VCEO	IC = -2 mA, IB = 0	-50			V
Collector-base cutoff current (Emitter open)	ICBO	VCB = -50 V, IE = 0			-0.1	μA
Collector-emitter cutoff current (Base open)	ICEO	VCE = -50 V, IB = 0			-0.5	μA
Emitter-base cutoff current (Collector open)	IEBO	VEB = -6 V, IC = 0			-0.2	mA
Forward current transfer ratio	hFE	VCE = -10 V, IC = -5 mA	60			-
Collector-emitter saturation voltage	VCE(sat)	IC = -10 mA, IB = -0.5 mA			-0.25	V
Input voltage	Vi(on)	VCE = -0.2 V, IC = -5 mA	-2.6			V
input voltage	Vi(off)	VCE = -5 V, IC = -100 µA			-0.8	V
Input resistance	R1		-30%	22	+30%	kΩ
Resistance ratio	R1/R2		0.8	1.0	1.2	-

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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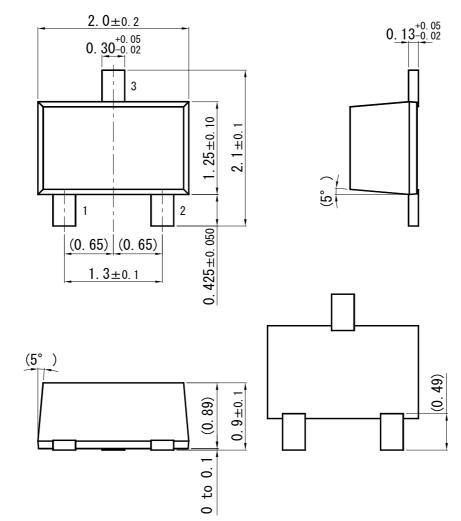
Output current Io (A)

Input voltage VIN (V)

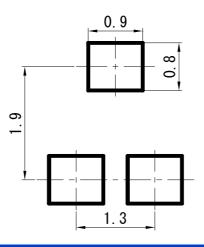


SMini3-F2-B

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■ Land Pattern (Reference) (Unit: mm)



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